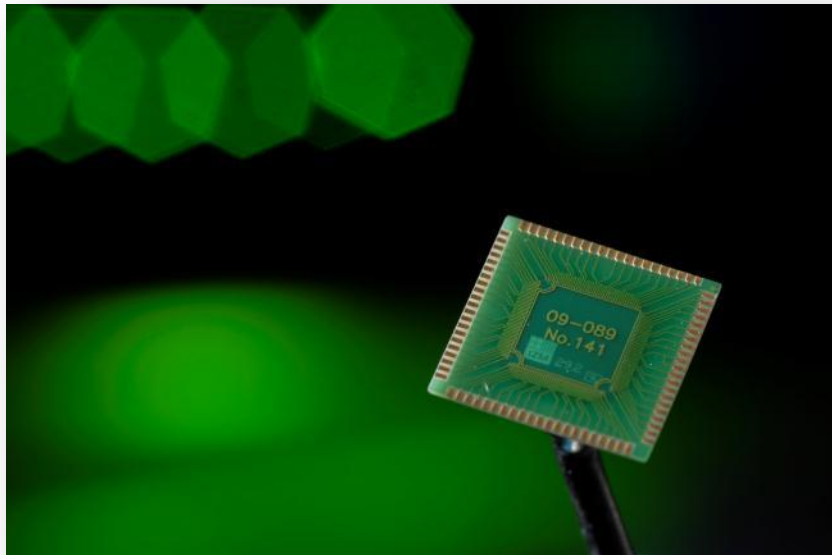
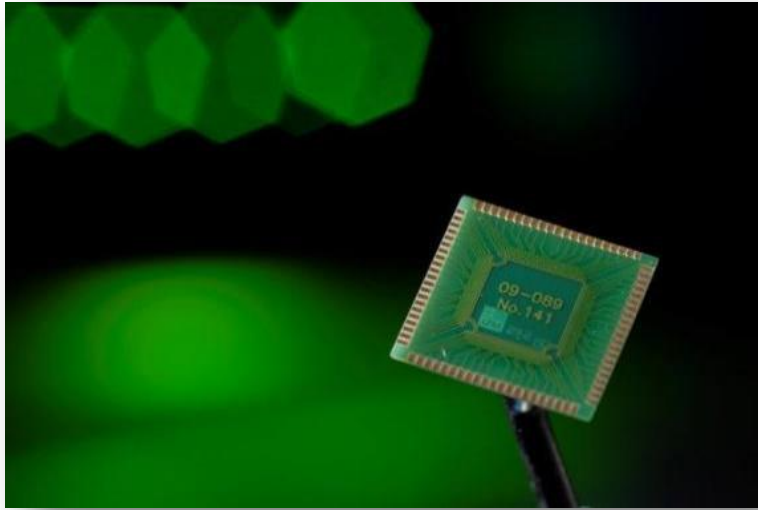


Embedded Power Modules – A new approach using Power Core and High Power PCB



- Lars Böttcher
- Fraunhofer IZM Berlin
- lars.boettcher@izm.fraunhofer.de



- Introduction
- Embedding for Power Semiconductors
- Automotive Power Systems – Project “**Hi-Level**”
- Power core embedding concept – Project “**EmPower**”
- Conclusion
- Acknowledgements



Power Packages

- Single chip packages for MOSFETs, IGBTs or diodes
- Use in lower power applications



Power Modules

- Use for mid and high power applications
- Include e. g. IGBTs and diodes in half bridge configuration
- Electrical isolation to backside

Power Chip Embedding - Opportunities

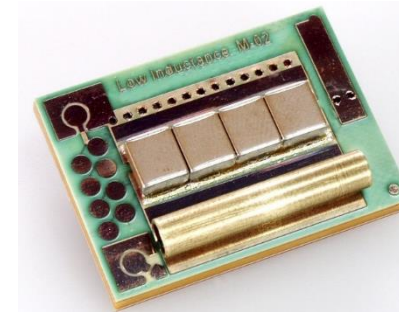
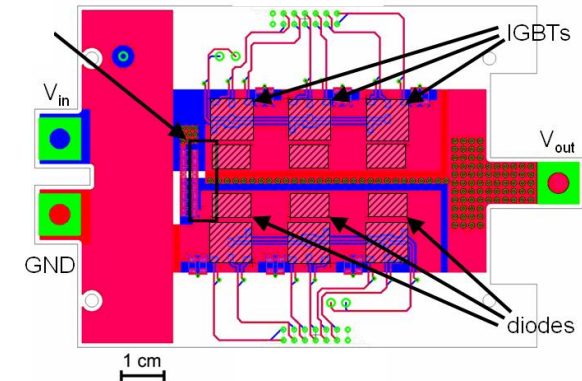
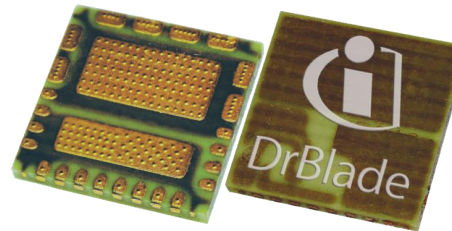
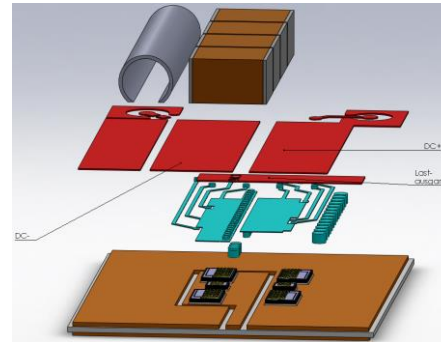
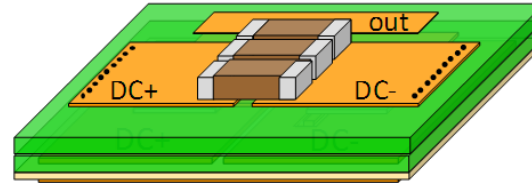
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wire bonding on DCB



- ➔ strong restriction of designs by technological limits
- ➔ Highly inductive connection by wire bonds

embedding

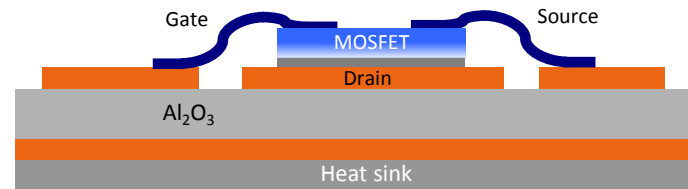


- ➔ Huge design space is open for exploration
- ➔ Improve electrical performance, low inductive connection to die

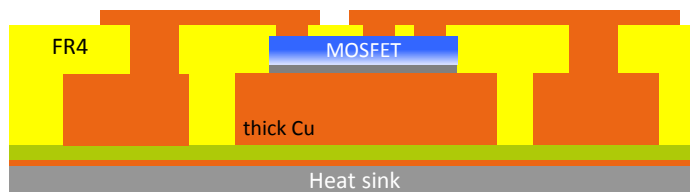
Embedded Power Modules

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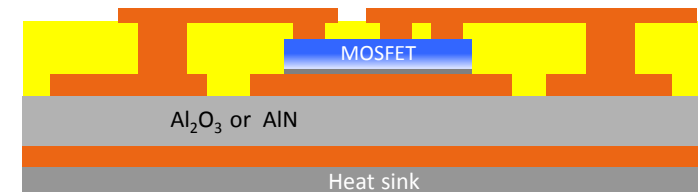
traditional power module



embedding on PCB substrate



embedding on ceramic substrate



■ Production panel 610x456 mm² (18"x24")

■ Isolation and thermal conduction by high- λ laminate

→ Low to medium power modules

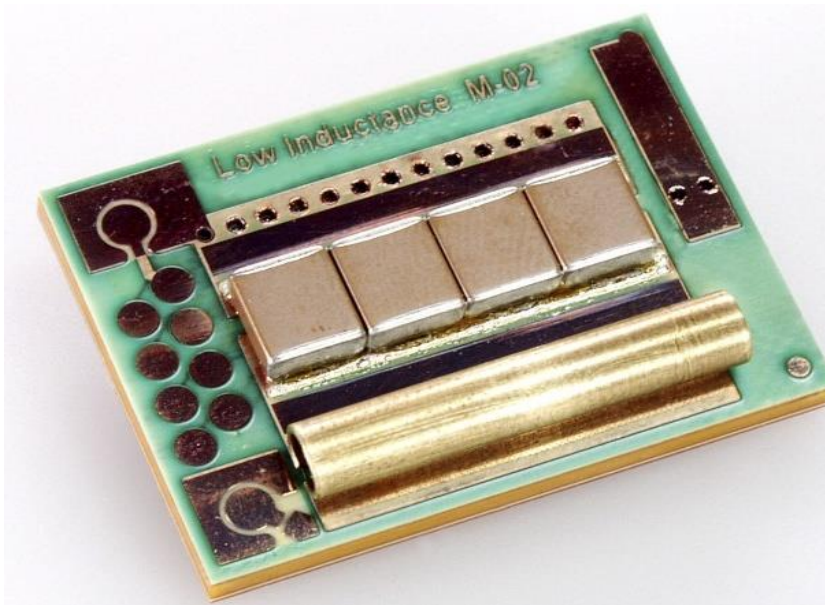
■ Production panel 125x175 mm² (5"x7")

■ Isolation and thermal conduction by Al₂O₃ or AlN DCB

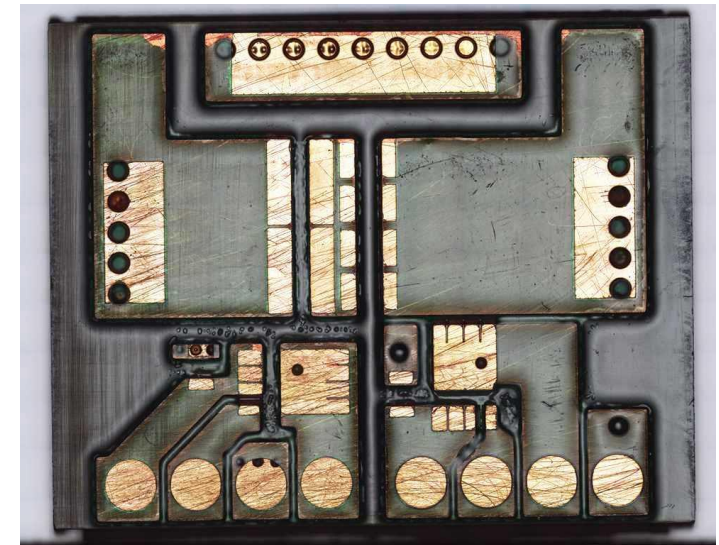
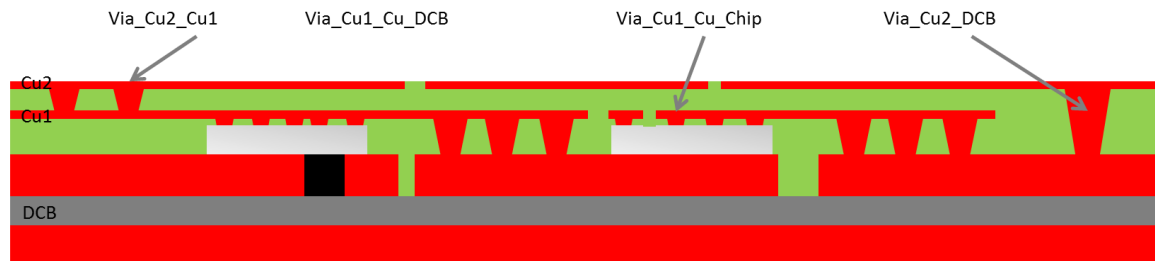
→ High power modules

DCB based, ultra low inductance module

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- Full bus bar structure using PCB Process on a DBC
- DC capacitors on the module
- DC link current measurement included



➔ DC-link inductance of 0.8 nH
Lowest possible inductance of conventional package: 10nH

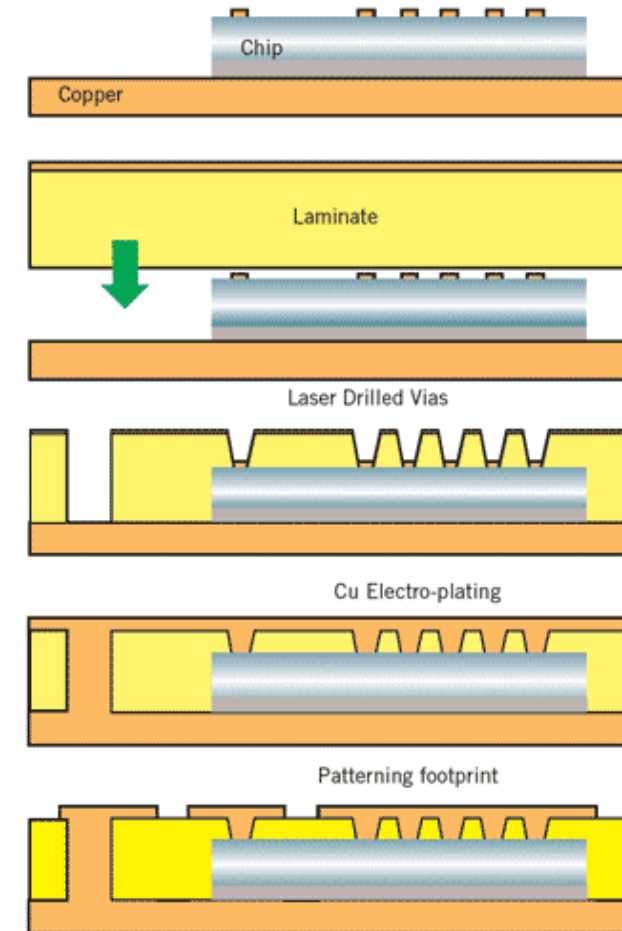
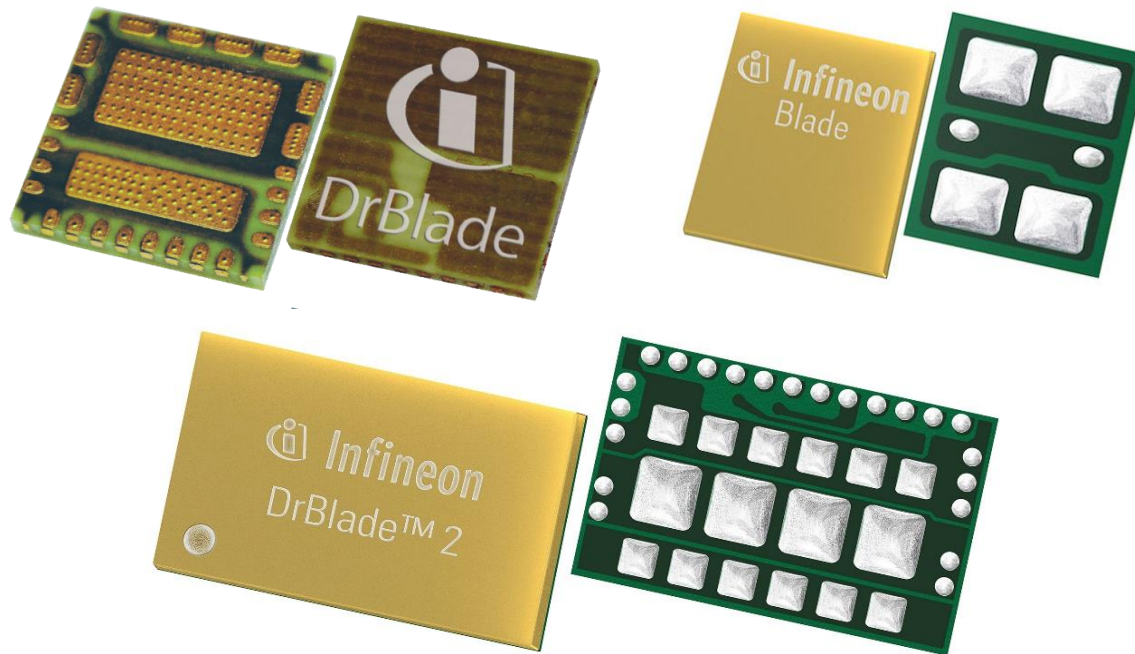
Products – Power Chip Packages & SiPs

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Blade power package

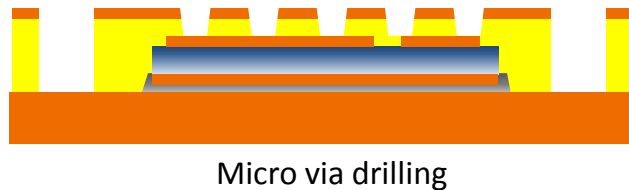
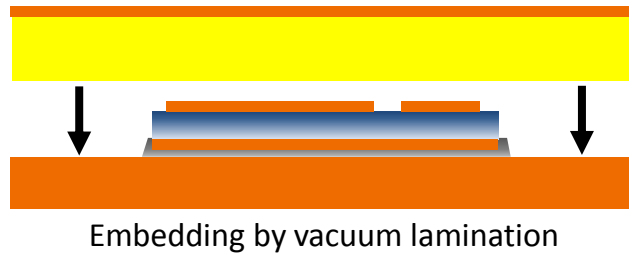
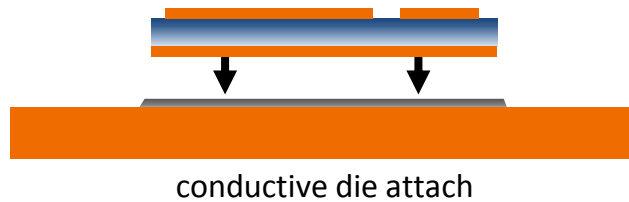
- Embedded MOSFET / Driver MOS
- Manufacturing on PCB format



Licensing and process transfer from Fraunhofer IZM

Power Chip Embedding – Face-up Process

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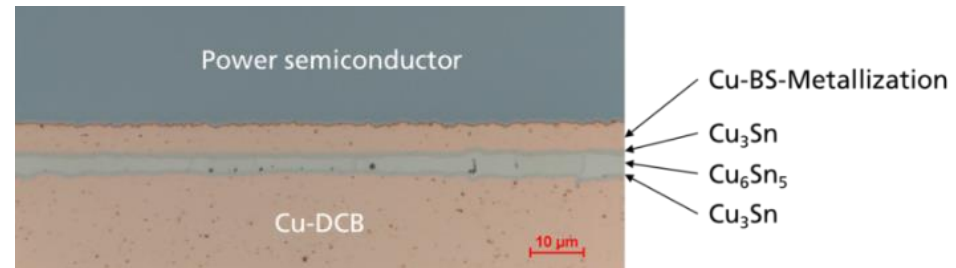
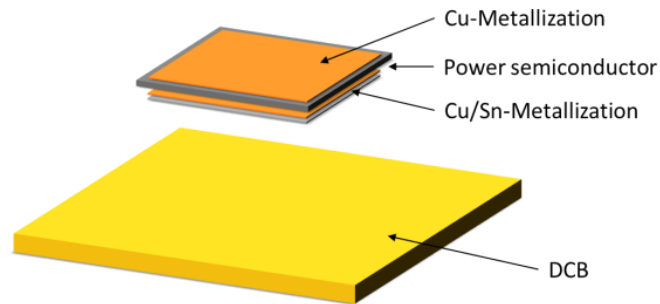
- Substrate: leadframe, copper foil, high current PCB
- Conductive die attach: various
- Embedding in FR4 prepreg layer:
 - Structured layers for dies
 - Full layer for top side isolation
 - Cu foil
- Blind via manufacturing:
 - Laser via to embedded die
 - Laser or mechanical drilling to substrate
- Cleaning, Activation and Cu metallization
- Patterning of circuitry

Power Chip Embedding – Die assembly

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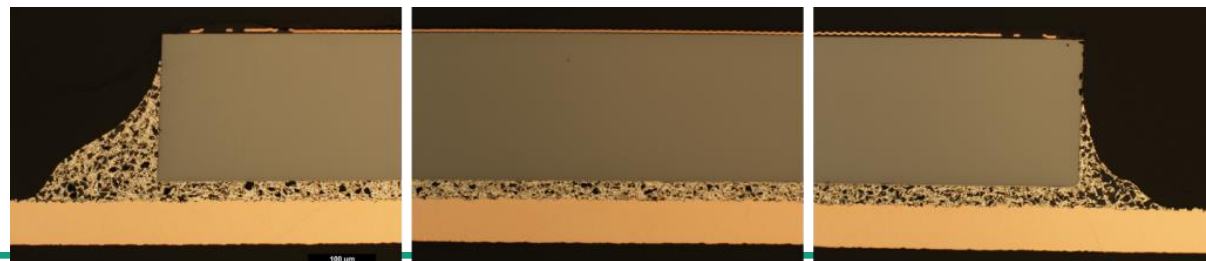
■ TLPB: transit liquid phase bonding:

- Good thermal and electrical conductivity
- Requires additional metallization on Wafer backside



■ Sinter glue:

- Easy to apply
- Limited electrical and thermal conductivity



Power Chip Embedding – Die assembly

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■ Ag sintering

- Good thermal and electrical conductivity
- Sinter paste application by printing or dispensing

■ Without pressure

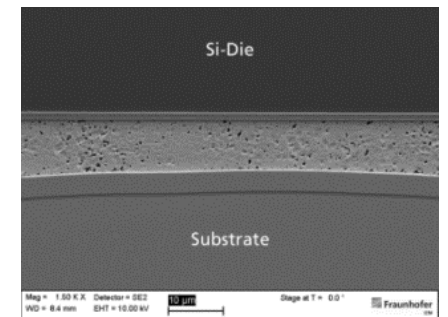
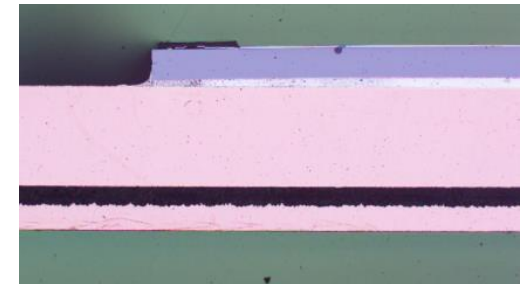
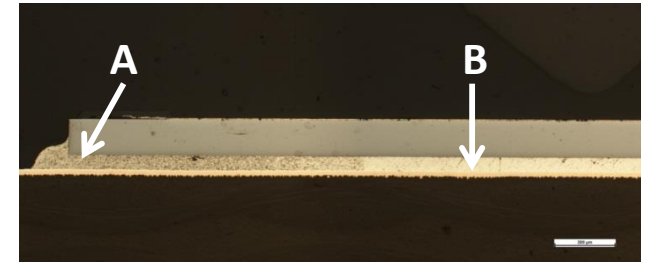
- Sintering in oven
- Reliability issues in TC

■ Low Pressure ($\leq 30\text{bar}$)

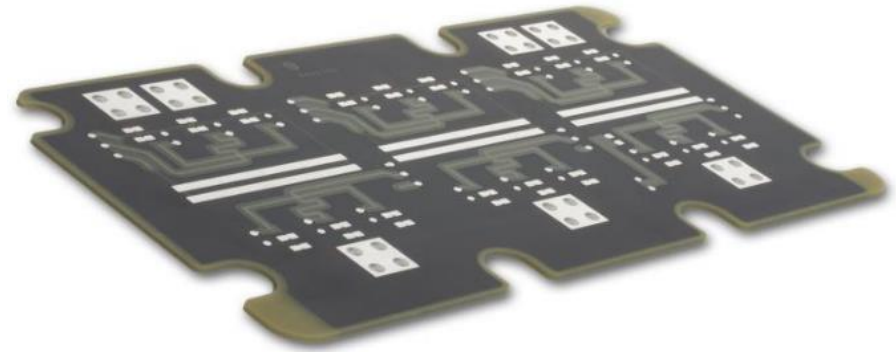
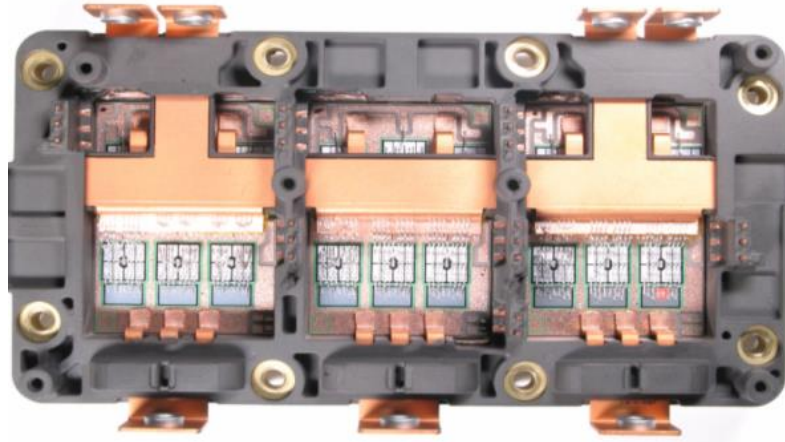
- Sintering in Multilayer press, capable for large substrates
- Process under development

■ Pressure

- Sintering in press, capable for small substrates



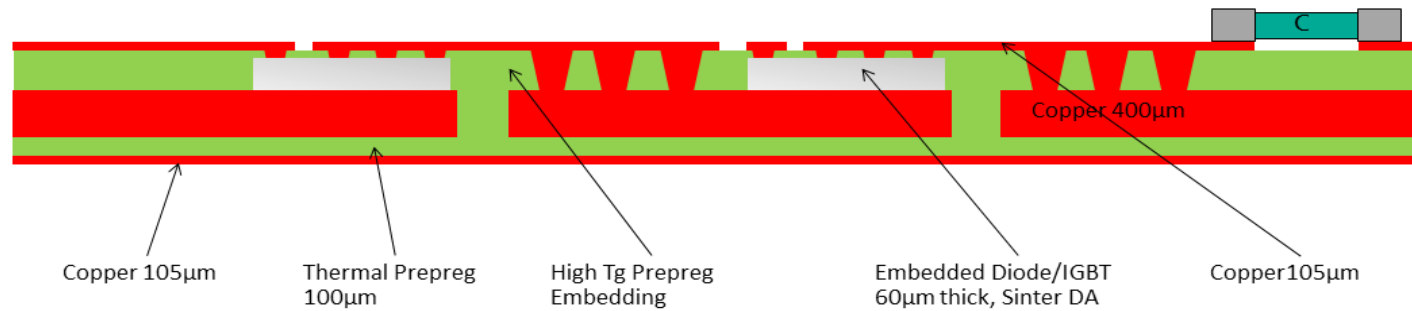
Development of planar power modules for motor inverter



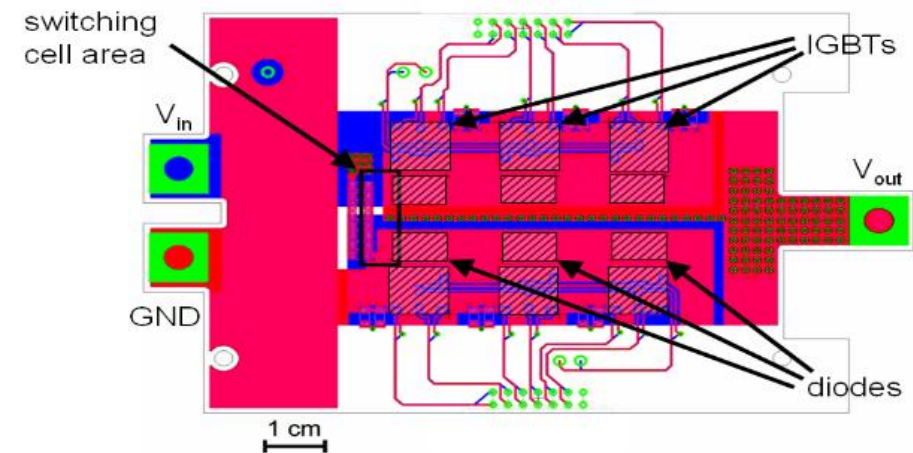
p² Pack, courtesy of Schweizer Electronic

Features

- Reduction of height by 10 mm
- Cost efficient production
- Manufacturing on panel format
- Integration of control electronics



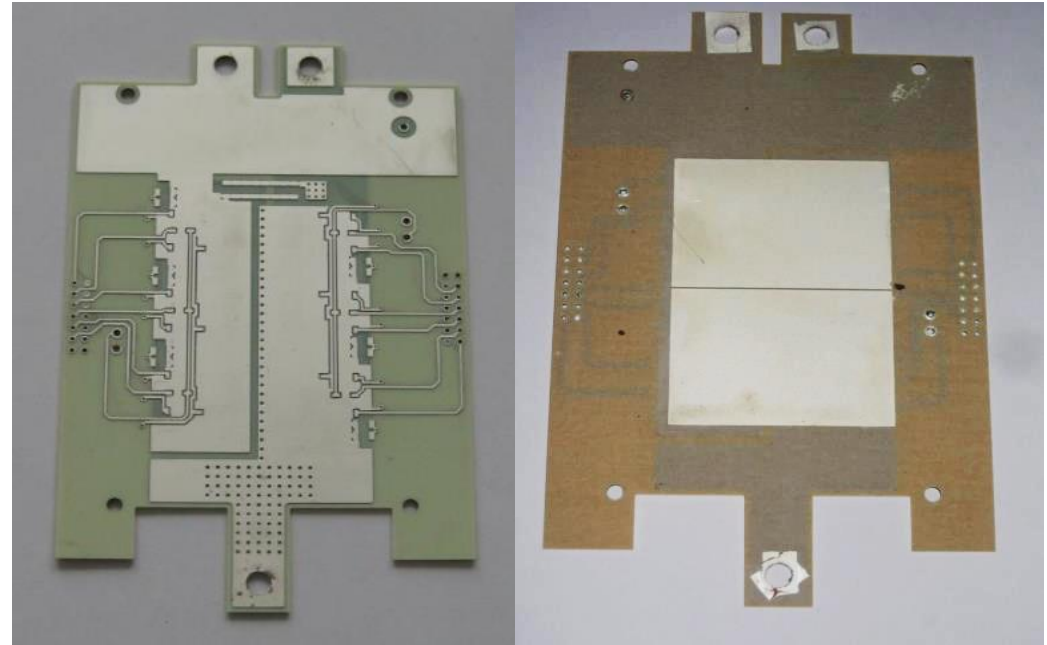
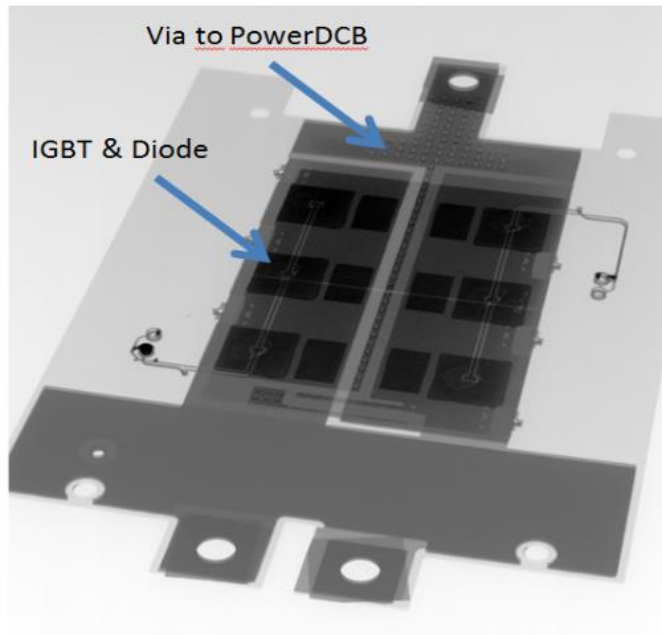
- Single phase, 20 – 660 VAC
- 2 IGBTs 200 A
- 2 freewheeling diodes
- IGBT and Diode on thick copper substrate



10 kW Demonstrator

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- 900µm thick module
- Six embedded IGBT and diodes
- DC link capacitors assembled on module



Schematic - 50 kW Demonstrator

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PROJECT HJ-LEVEL

Design/Setup/
Test:

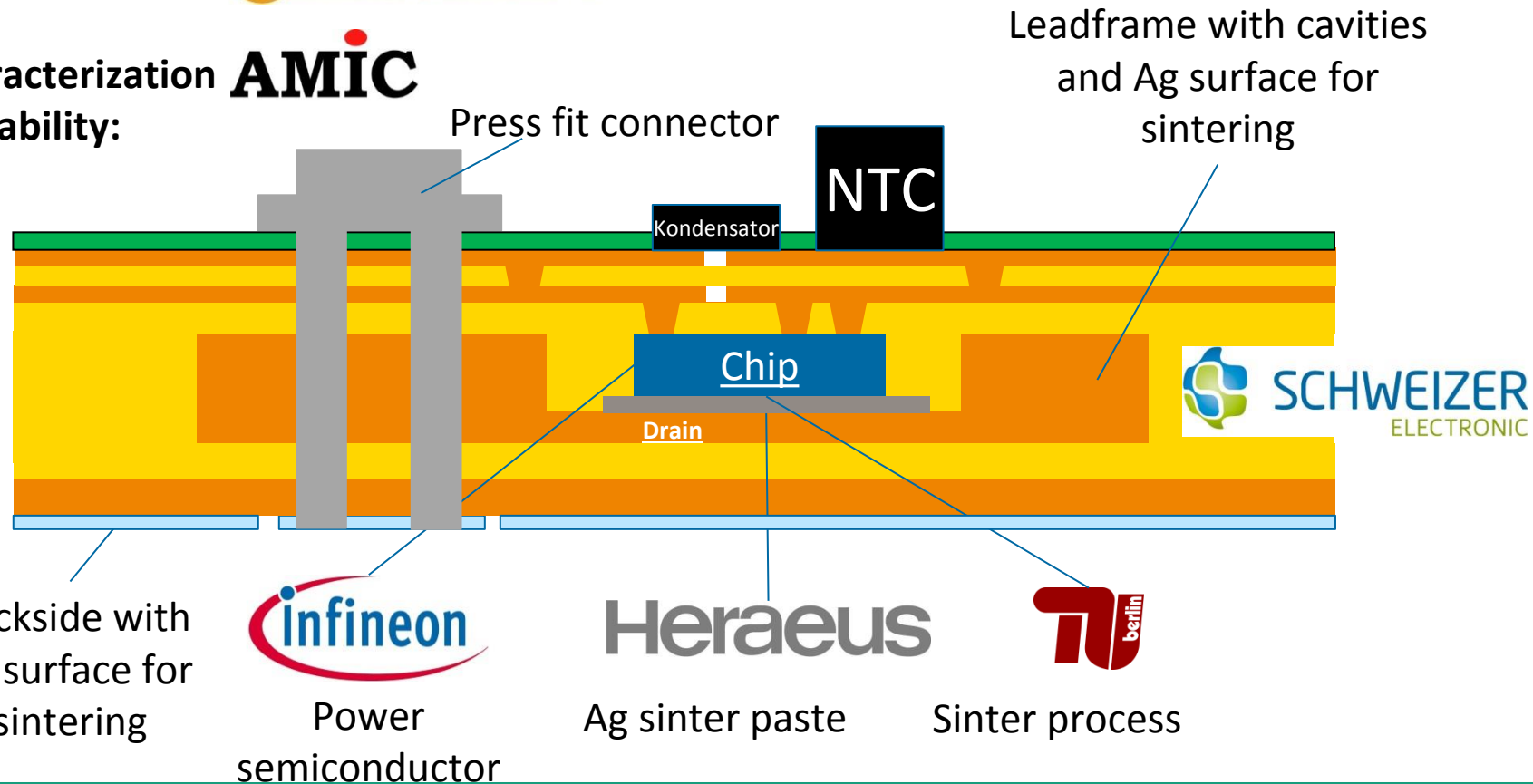


Test/
End user:

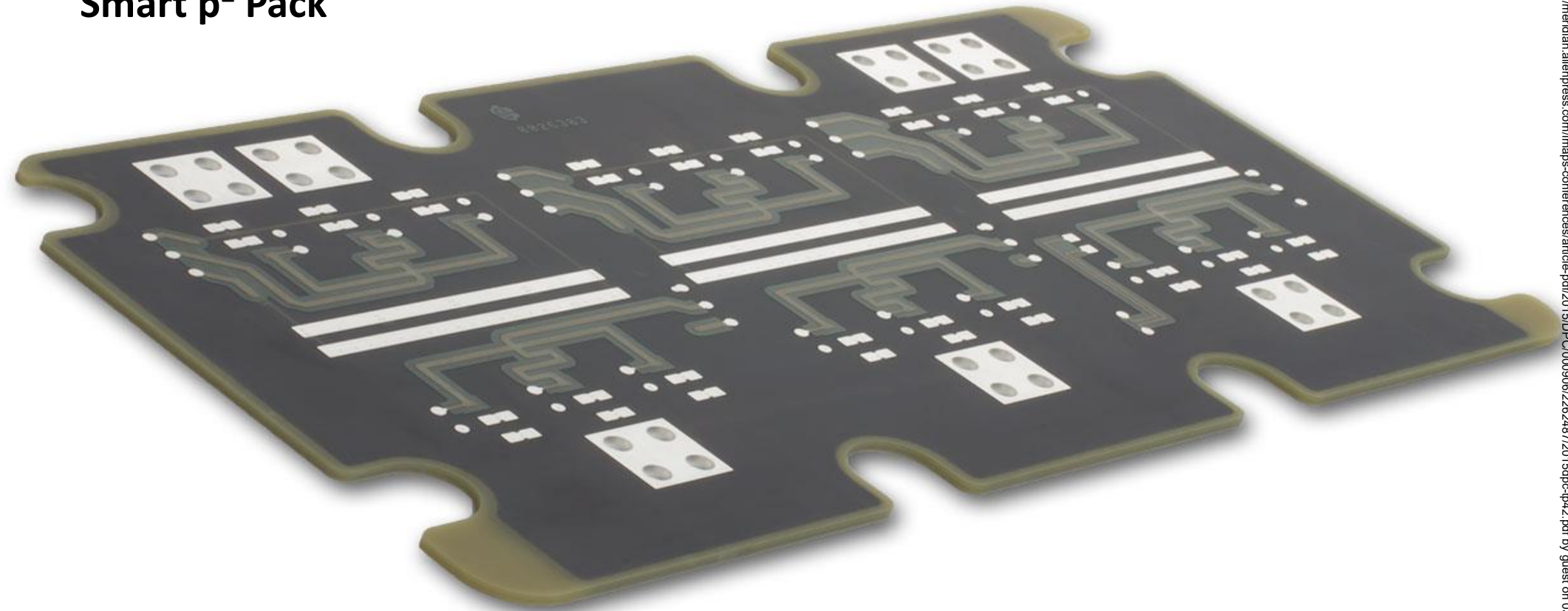
DAIMLER

Characterization
/reliability:

AMIC



Smart p² Pack

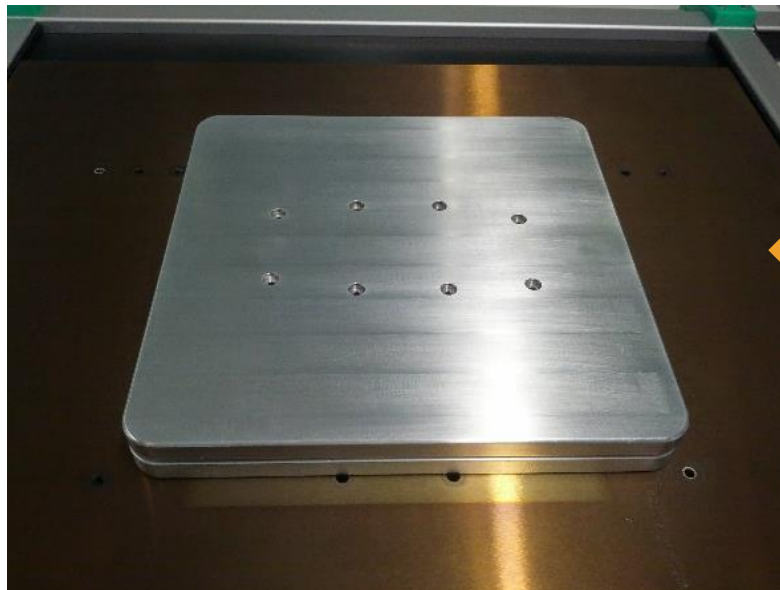
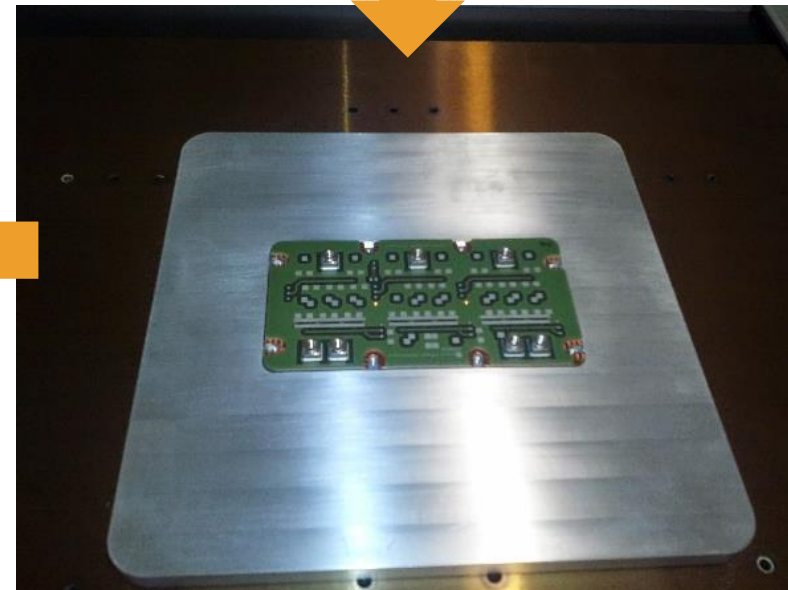
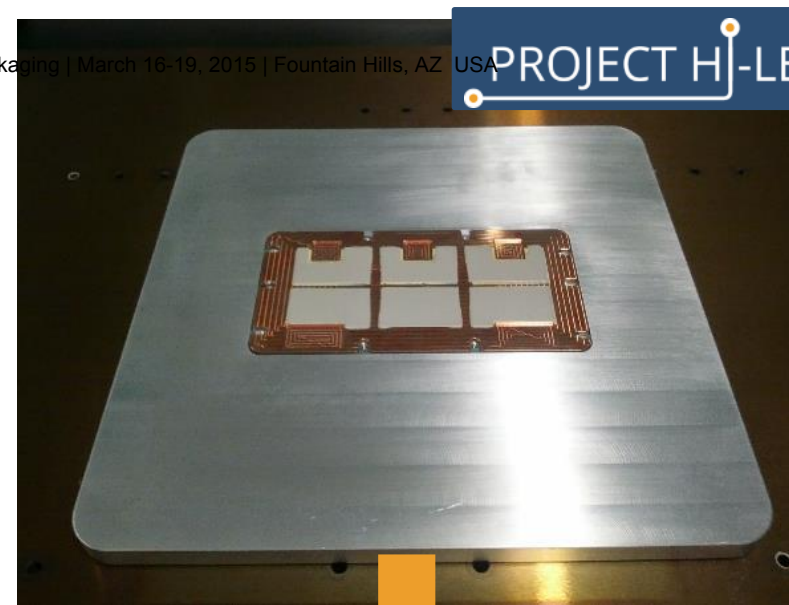


Sintering to heat sink

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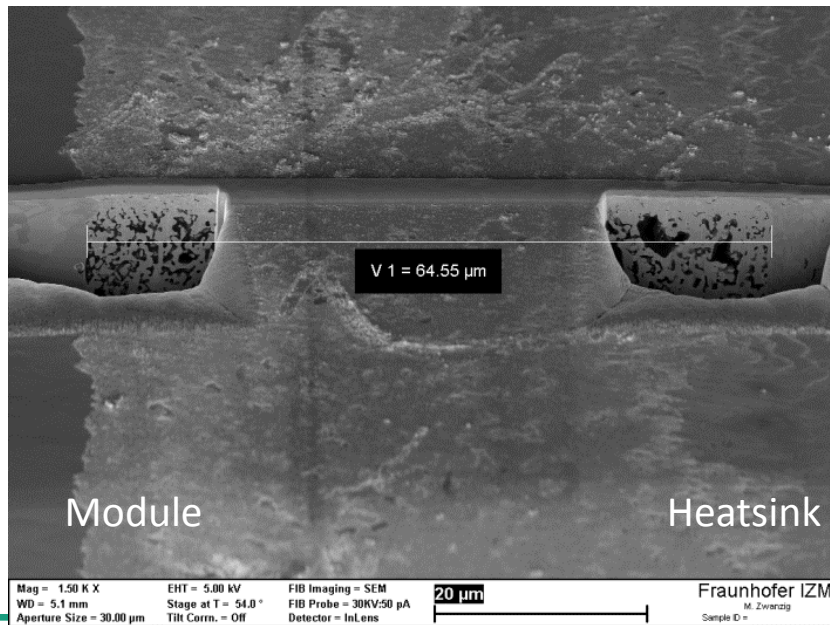
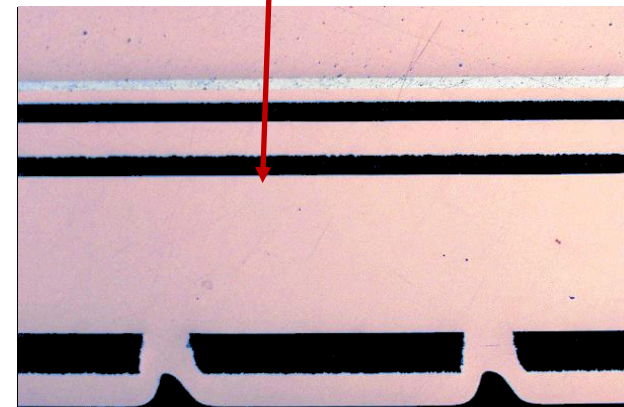
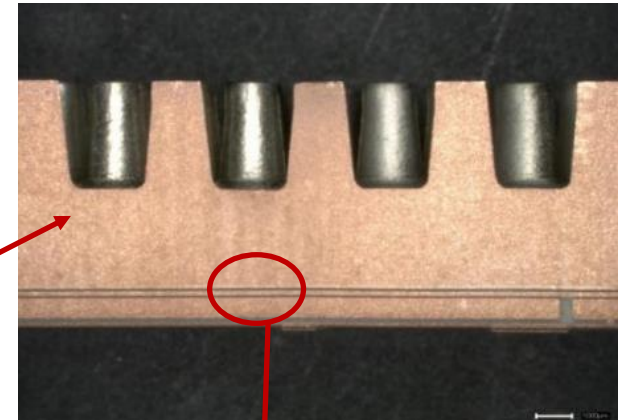
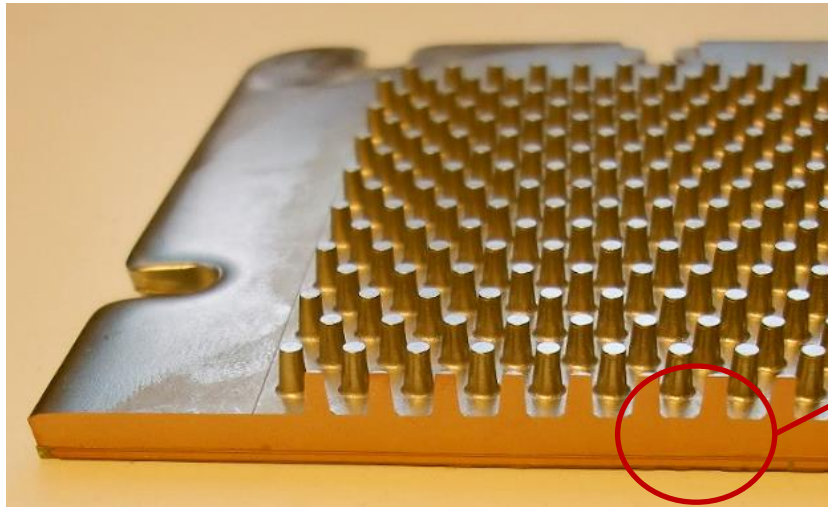
PROJECT HJ-LEVEL

- Printing of Ag sinter paste
- Sintering at low pressure (3 MPa) in Multilayer press
- Parallel sintering of modules possible

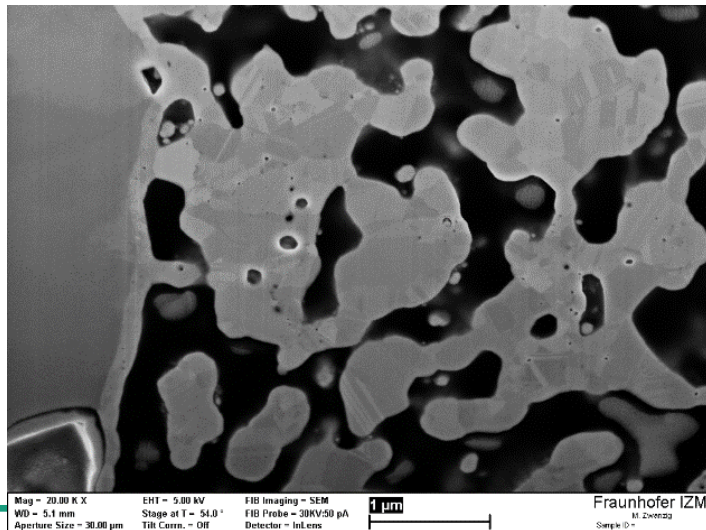
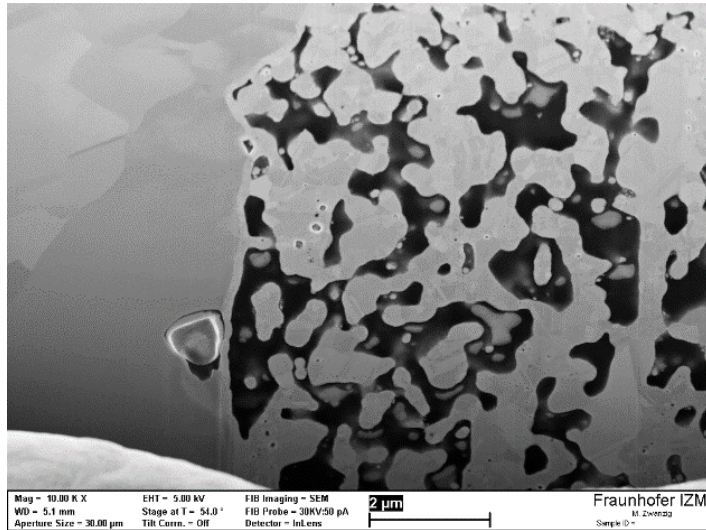


Sintering to heat sink

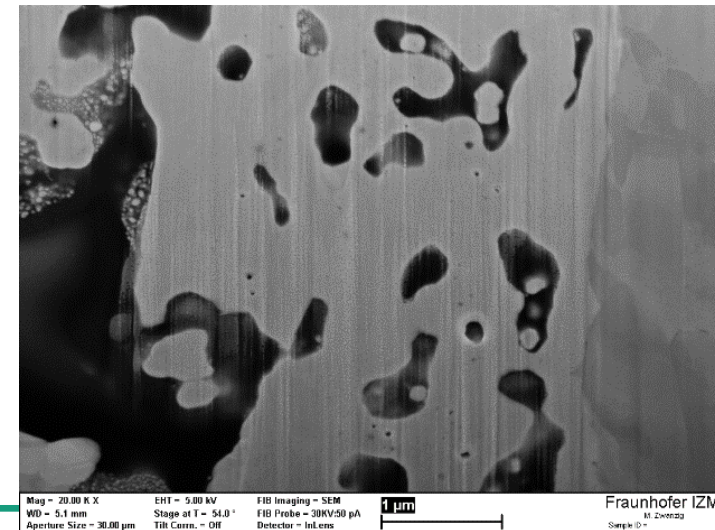
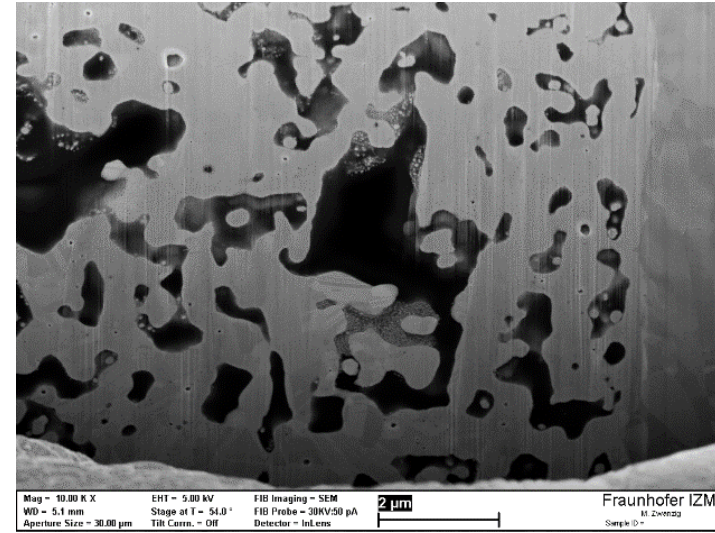
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Interface Modul



Interface heat sink



- **Embedded power** components for electric vehicle applications
- Started in September 2013, duration 3 years
- Project goals:
 - Industrialize double sided copper plating on wafer level
 - Industrialize next generation automotive power modules
- Benefits:
 - High performance power products with embedded MOSFET, IGBT, GaN, etc.
 - Smallest form factor power supplies
- Partners:

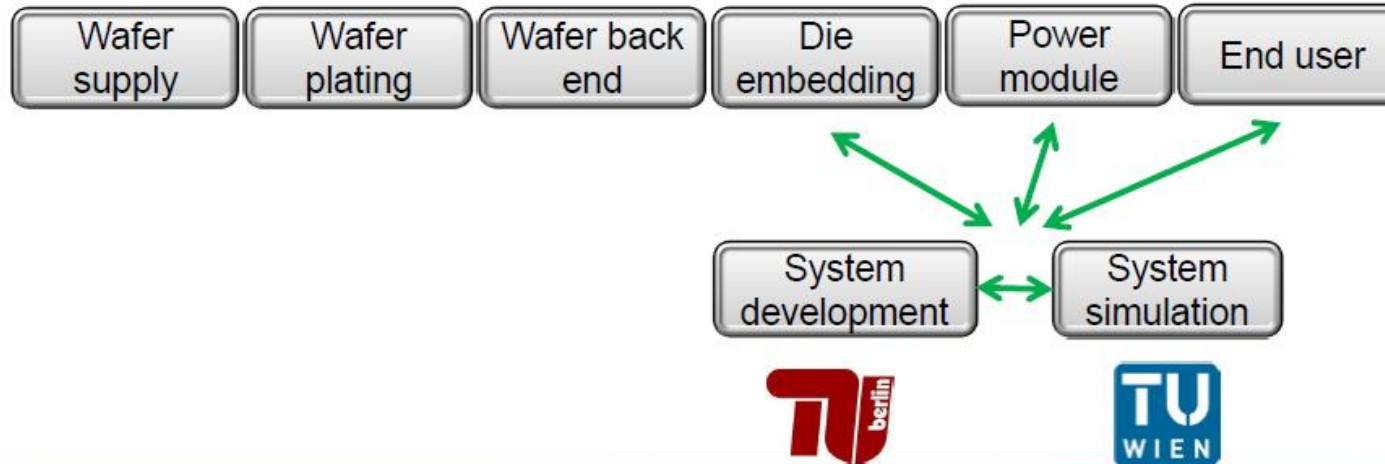


<http://catrene-empower.ats.net>

EmPower Consortium



Duration: Sept. 2013 – Aug. 2016
 Project Coordinator: AT&S
 Project budget: 5,6 Mio €



EmPower – CATRENE | Bayern Innovativ 27.1.2015 | Hannes Stahr

10

Source: Hannes Stahr, AT&S,
 Bayern Innovativ Jan 2015

- Power class 50W:
 - Power package for fast rectifier diode
 - Demonstrator for embedded power core (AT&S and IZM/TUB)
- Power class 500W
 - Power module for pedelec application
 - Demonstrator for double sided cooled power module
 - Benchmark with existing concept
- Power class 50kW
 - Power module for HEV / EV application
 - Benchmark with existing module



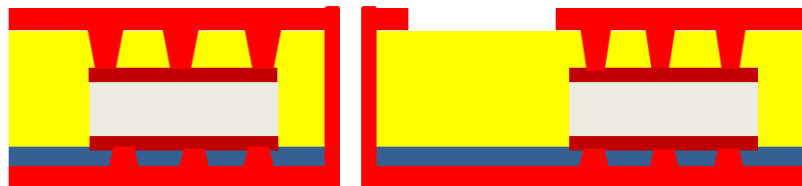
(1) Die Placement



(2) Layup and lamination of PP



(3) Via formation to embedded die



(4) Cu metallization and patterning

- Epoxy coated foil or prepreg and Cu foil used
- No use of sintered or soldered die attach
- Direct micro via connection from top and bottom side
- Requires double sided Cu metallization of semiconductor

Power core concept – process

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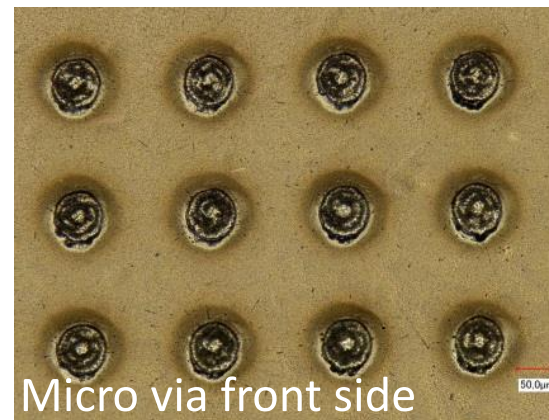
■ Substrate

- Cu foil with B-stage epoxy resin
- Cu foil and thin prepreg

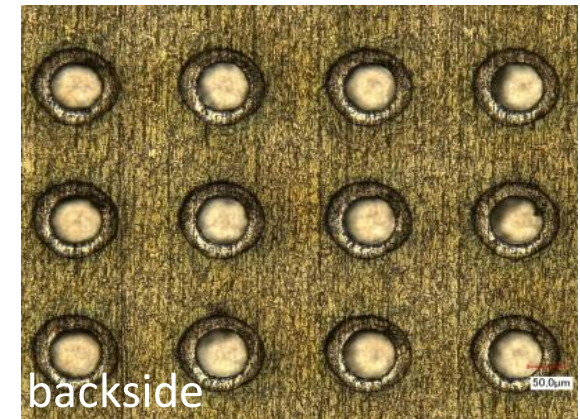
■ Die attach with heated tool

- Die at fixed position
- But resin still needs to be reactive to bond to additional layers during embedding

■ Laser drilling to embedded die top and back



Micro via front side

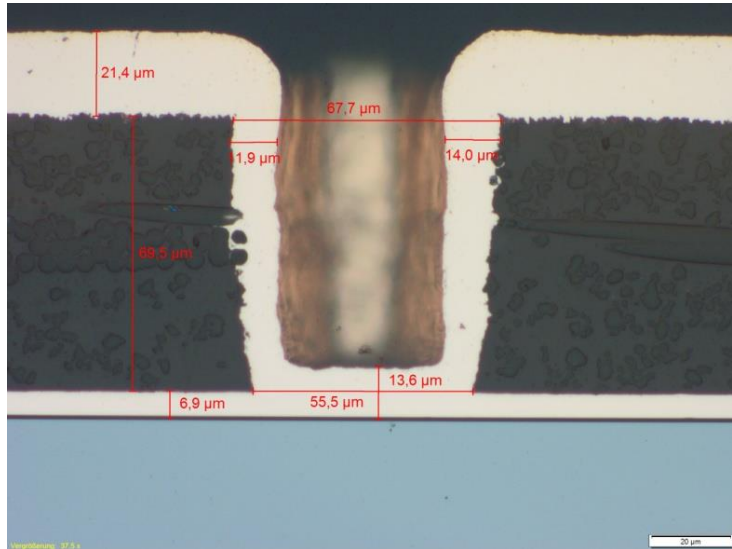
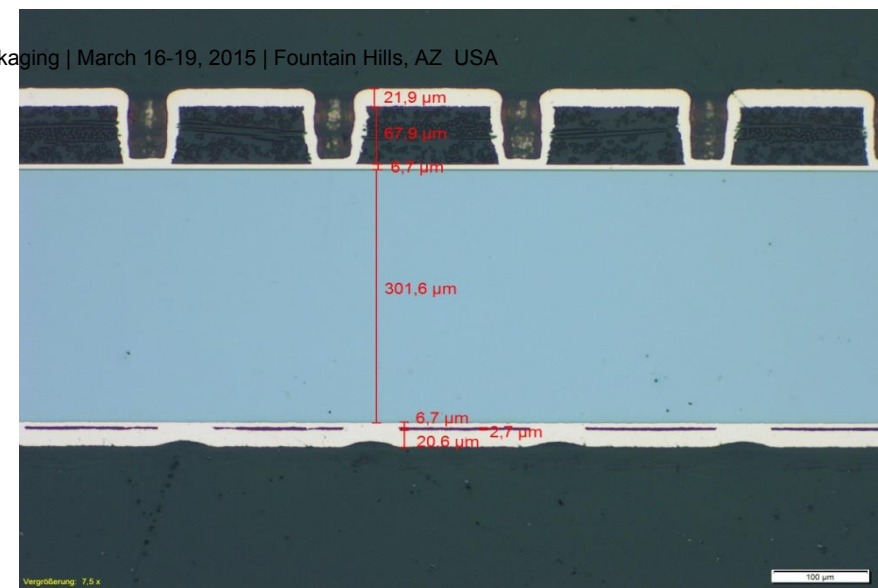


backside

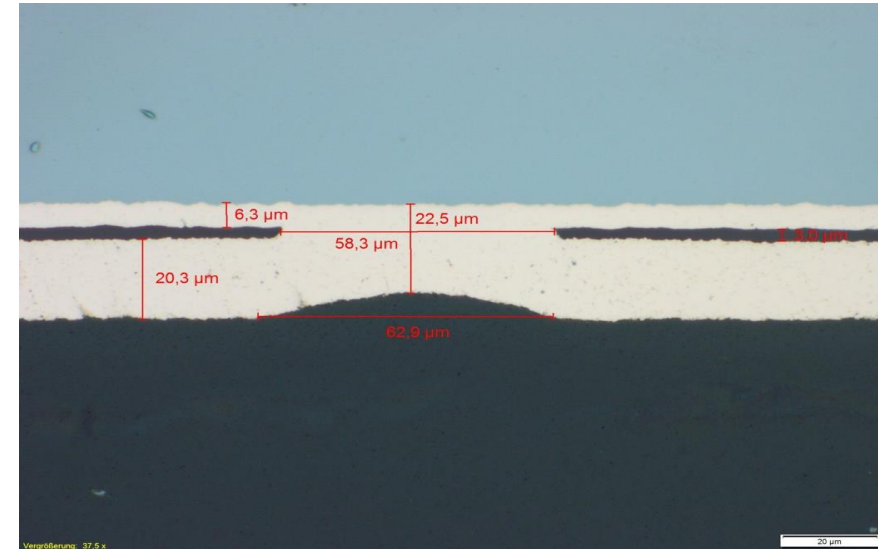
Power core concept – results

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- Plated copper connection to top and backside contact



cross section micro via front side

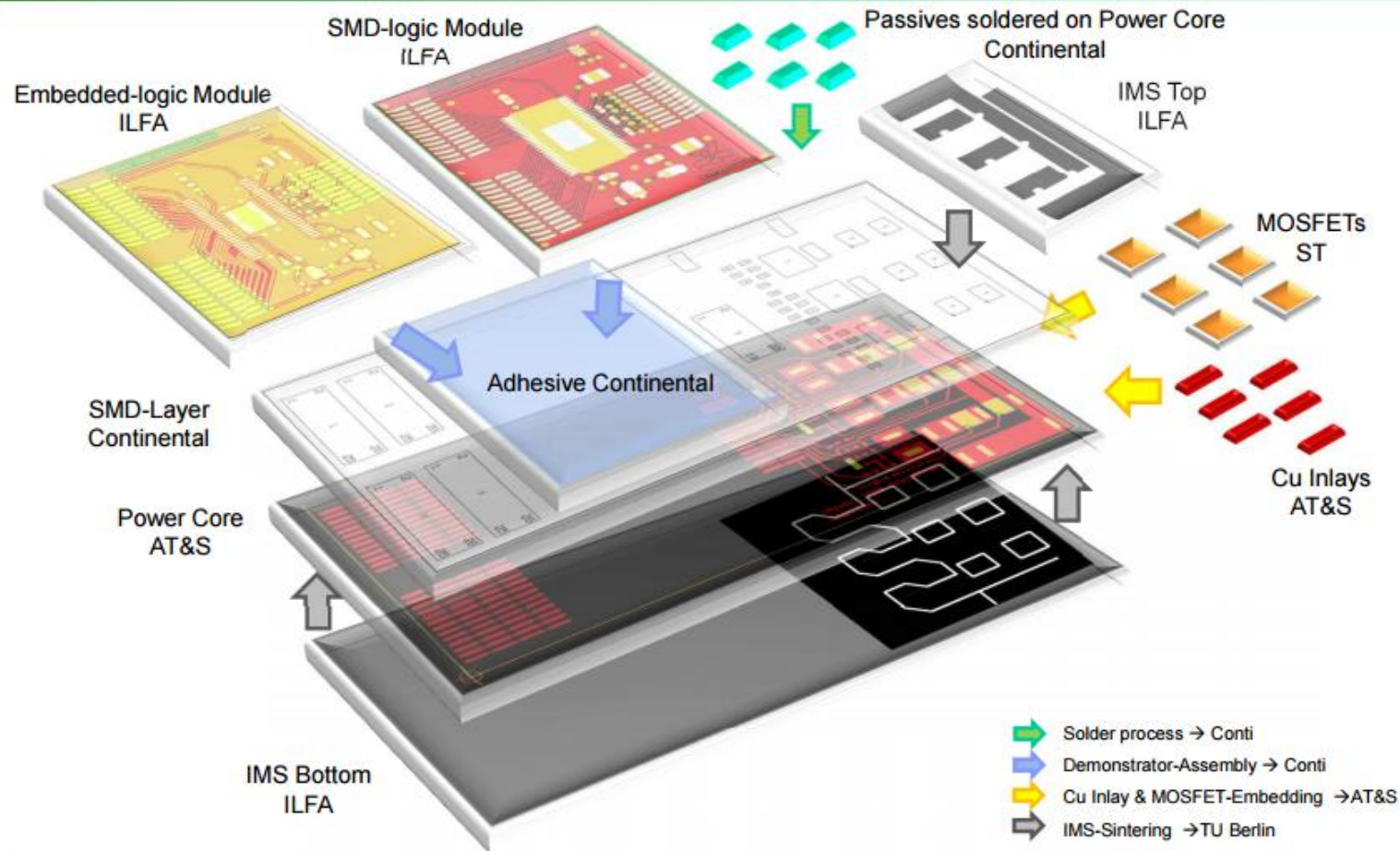


back side

500 W Demonstrator

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WP5 D5.5 / Task 5.3 Power module development



EmPower | GM4 / WP5 Status | Berlin 10.-11. March 2015 | M. Morianz



Source: Mike Morianz, AT&S
EmPower Konsortium

High current connection

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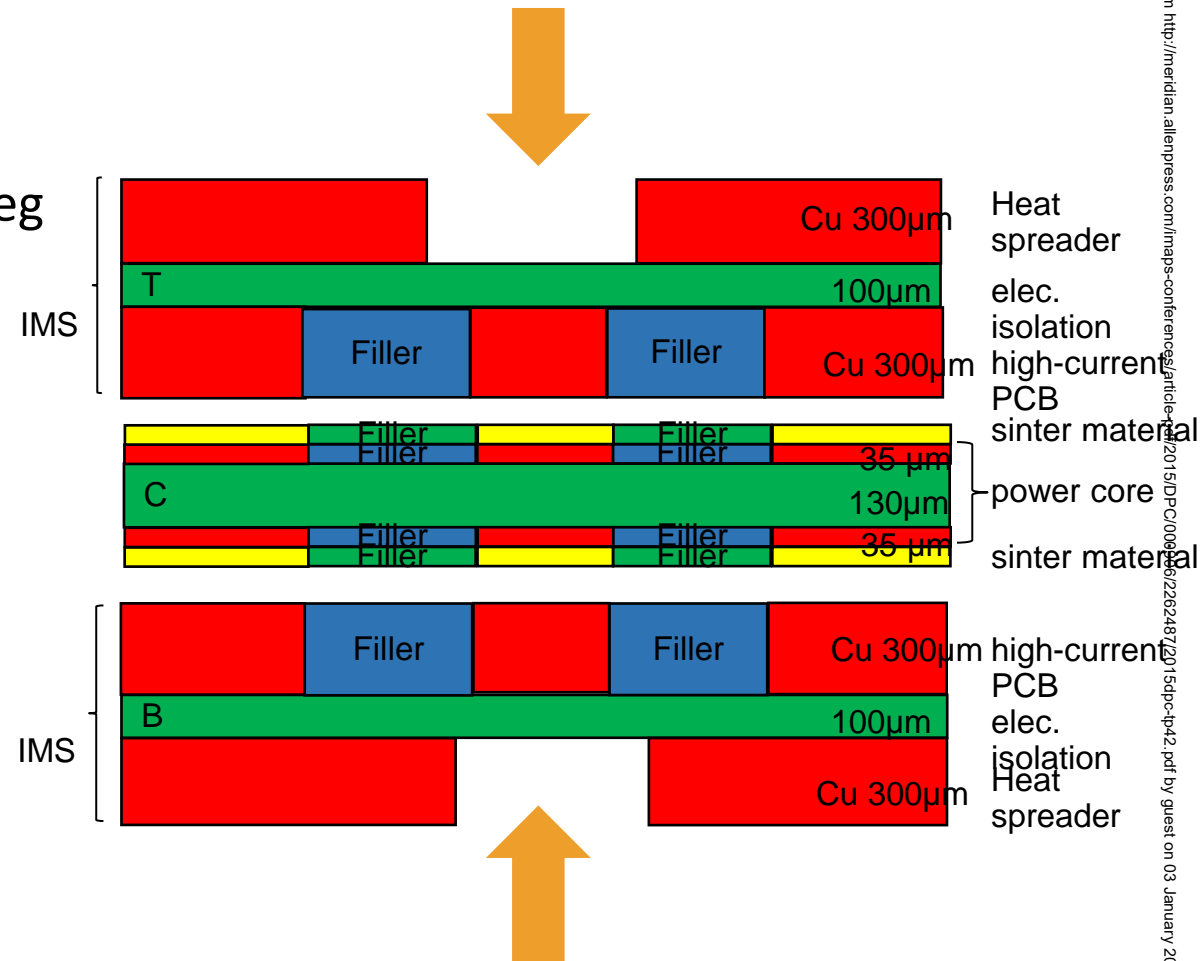
■ Connection of power core to IMS substrate

- Organic substrate with 300μm Cu layer

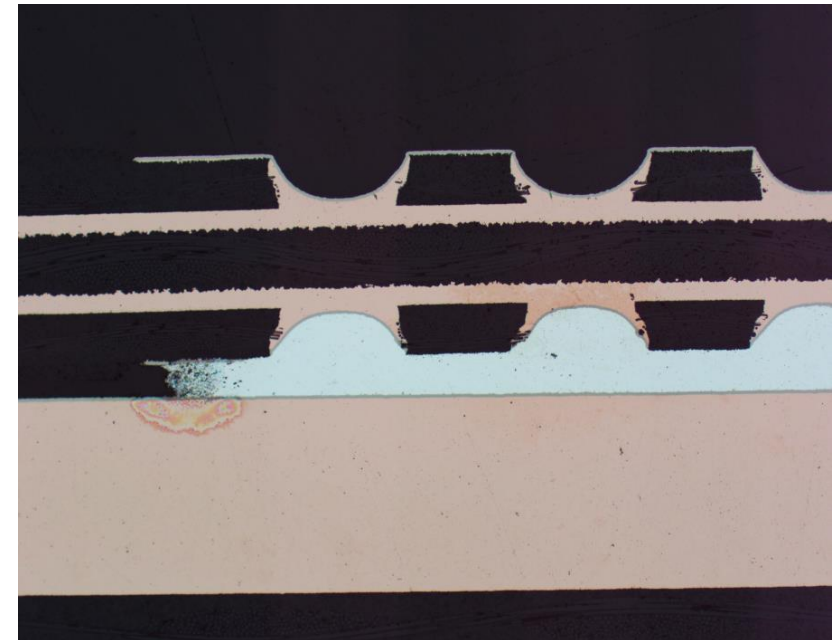
- High thermal conductive prepreg

■ Connection of power core to IMS substrate

■ Ag sintering on substrate level

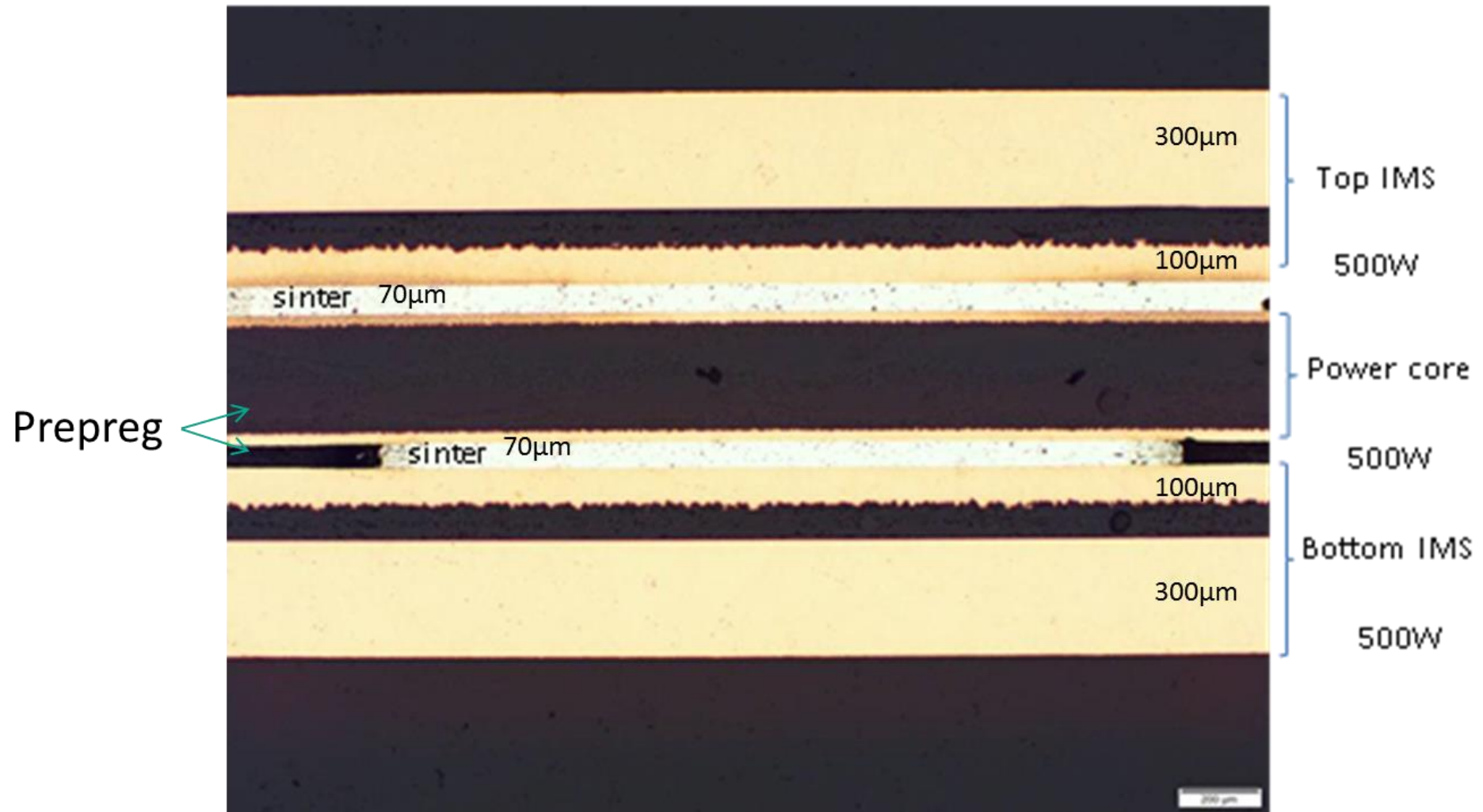


- Printing of Ag sinter paste
- Structured prepare layers for filling gap between power core and IMS
- Sintering in multilayer press
 - Void free sintering of power core and IMS
 - Void free filling of gap with epoxy resin
 - Sintering and curing in the same process



High current connection – 500 W demonstrator

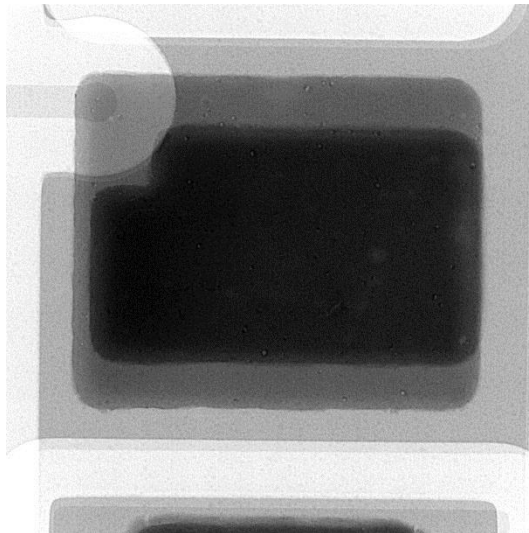
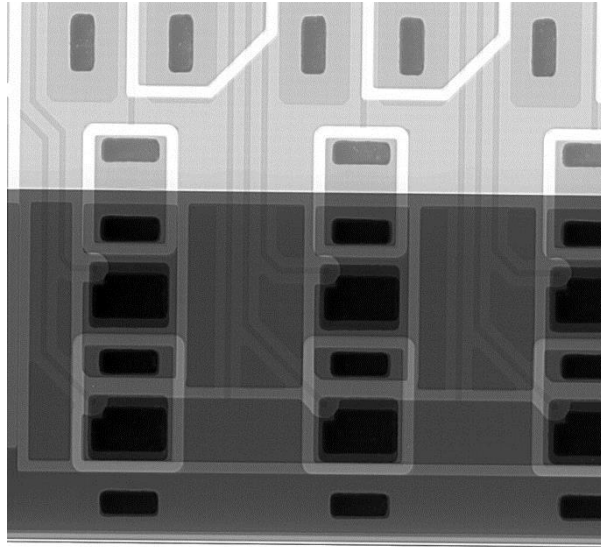
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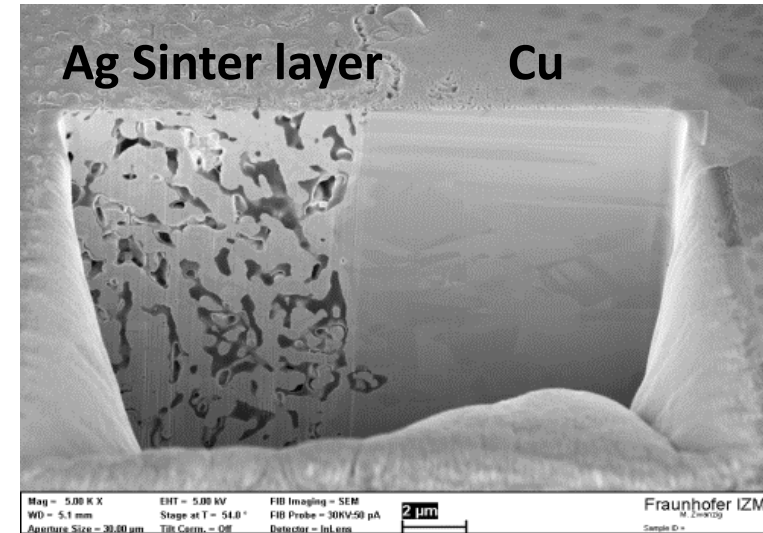
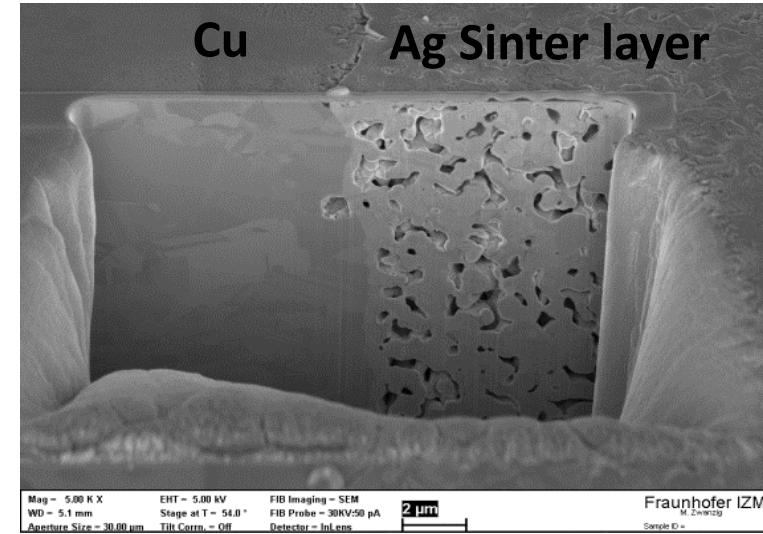
High current connection – 500 W demonstrator

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x-ray analysis



FIB analysis



- The embedding of components for the realization of power packages and modules provides a flexible platform for a lot of different applications
- The Hi-Level project demonstrated the successful manufacturing and electrical test of power modules up to 50kW switching power
- The EmPower project focuses on a new approach for the embedding of power semiconductors using double sided copper connections to the embedded die (power core) and IMS substrates for high current and thermal management
- Use of power core avoids soldering or Ag sintering of the power semiconductors and the handling of thick copper substrates during the embedding process.

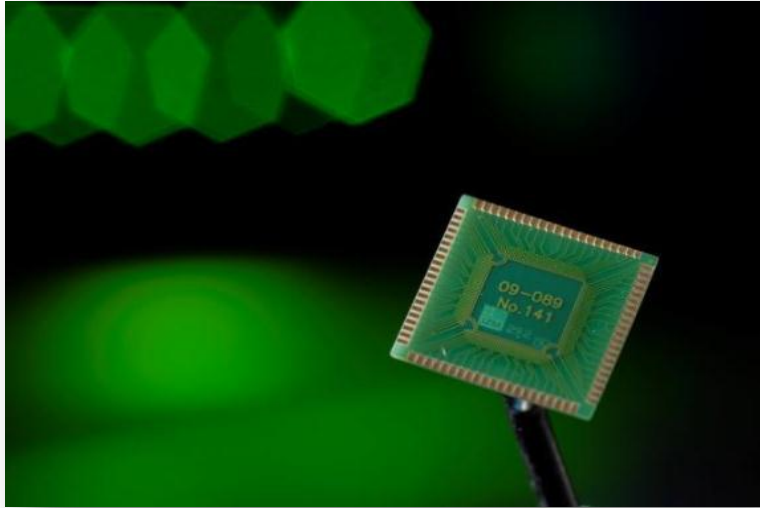


- German “Federal Ministry of Education and Research” for the financial support of the “HI-LEVEL” project (FKZ 13N11651) and the partners within the project
- German “Federal Ministry of Education and Research” for the financial support of the “EmPower” project (FKZ 16EKF0016), which is also supported in the European “Catrene” program (CT315 – EmPower) and the partners within the project

GEFÖRDERT VOM



Bundesministerium
für Bildung
und Forschung



Thank you very much for your attention!

Contact: Lars.Boettcher@izm.fraunhofer.de